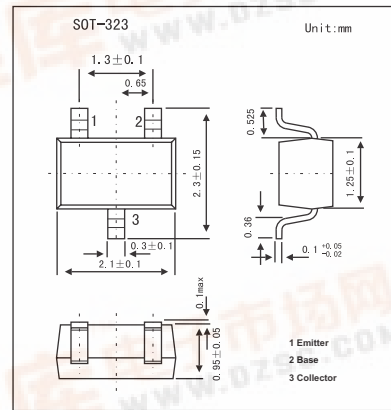


SMD Type Transistors

Silicon NPN Epitaxial Planar  
2SC3936

■ Features

- Optimum for RF amplification, oscillation, mixing, and IF of FM/AM radios.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	20	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	30	mA
Collector power dissipation	P <sub>c</sub>	150	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V <sub>CB0</sub>	I <sub>c</sub> = 10 μA, I <sub>E</sub> = 0	30			V
Collector-emitter voltage	V <sub>CEO</sub>	I <sub>c</sub> = 2 mA, I <sub>B</sub> = 0	20			V
Emitter-base voltage	V <sub>EB0</sub>	I <sub>E</sub> = 10 μA, I <sub>c</sub> = 0	5			V
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = 10 V, I <sub>c</sub> = 1 mA	70		250	
Transition frequency	f <sub>T</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = -1 mA, f = 200 MHz	150	230		MHz
Reverse transfer capacitance	C <sub>re</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = -1 mA, f = 10.7 MHz		1.3		pF

■ hFE Classification

Marking	KB	KC
hFE	70~160	110~250

